

# Study of Lithographic Parameters for the Trilayer Resist Systems in Electron Beam Lithography

Robert Andok<sup>1</sup>, Katia Vutova<sup>2, b)</sup>,  
Anna Konecnikova<sup>1</sup>, Mario Ritomsky<sup>1</sup> and Ivan Kostic<sup>1, a)</sup>

<sup>1</sup>*Institute of Informatics, Slovak Academy of Sciences, Dubravska cesta 9, 845 07 Bratislava, Slovak Republic*

<sup>2</sup>*Institute of Electronics, Bulgarian Academy of Sciences, 72 Tzarigradsko chaussee blvd., Sofia 1784, Bulgaria*

<sup>a)</sup> *Corresponding authors: ivan.kostic@savba.sk*

<sup>b)</sup> *katia@van-computers.com*

**Abstract.** This paper focus on EBL experimental investigation and simulation of single/multilayer resists for pattern transfer. Important EBL process parameters such as solubility rates, resolution, absorbed energy in the pattern concerning investigated single and trilayer PMMA and HSQ resist systems are studied and discussed.